附表 3-2：

# 批准证书附件

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| № | Products, Materials | Items,Parameter | | Title, Code of specification, standard or method used | Restriction or limitation | measuring capacity | Note |
|---|---|---|---|---|---|---|---|
| | | 序号 | 名称 | | | | |
| 1 | IC（MOS random access memories） | 1 | ALL “0 ” and “1 ” function test | Semiconductor devices Integrated circuits Part 2:Digital integrated circuits GB/T 17574-1998 | Accredited only for: Voltage:-1V~6V Current:-200mA~200mA Maximum 512 channels | Power current: 0mA~1A Maximum frequency: 0HZ~800MHZ | |
| | | 2 | Function test of calibration board | Semiconductor devices Integrated circuits Part 2:Digital integrated circuits GB/T 17574-1998 | Accredited only for: Voltage:-1V~6V Current:-200mA~200mA Maximum 512 channels | Power current: 0mA~1A Maximum frequency: 0HZ~800MHZ | |
| | | 3 | Output high level voltage $V_{OH}$ | Semiconductor devices Integrated circuits Part 2:Digital integrated circuits GB/T 17574-1998 | Accredited only for: Voltage:-1V~6V Current:-200mA~200mA Maximum 512 channels | Power current: 0mA~1A Maximum frequency: 0HZ~800MHZ | |
| | | 4 | Output low level Voltage $V_{OL}$ | Semiconductor devices Integrated circuits Part 2:Digital integrated circuits GB/T 17574-1998 | Accredited only for: Voltage:-1V~6V Current:-200mA~200mA Maximum 512 channels | Power current: 0mA~1A Maximum frequency: 0HZ~800MHZ | |
| | | 5 | Input load current $I_{LI}$ | Semiconductor devices Integrated circuits Part 2:Digital integrated circuits GB/T 17574-1998 | Accredited only for: Voltage:-1V~6V Current:-200mA~200mA Maximum 512 channels | Power current: 0mA~1A Maximum frequency: 0HZ~800MHZ | |

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| | | 6 | Operative state power current $I_{cc}$ | Semiconductor devices Integrated circuits Part 2:Digital integrated circuits GB/T 17574-1998 | Accredited only for: Voltage:-1V~6V Current:-200mA~200mA Maximum 512 channels | Power current: 0mA~1A Maximum frequency: 0HZ~800MHZ | |
| | | 7 | Maintain state power current $I_{ccs}$ | Semiconductor devices Integrated circuits Part 2:Digital integrated circuits GB/T 17574-1998 | Accredited only for: Voltage:-1V~6V Current:-200mA~200mA Maximum 512 channels | Power current: 0mA~1A Maximum frequency: 0HZ~800MHZ | |
| 2 | IC（voltage regulators） | 1 | Output voltage $V_o$ | Semiconductor integrated circuits.Measuring method of voltage regulators GB/T 4377-2018 | Accredited only for: Voltage:-40V~40V Current:-1A~1A Maximum 48 channels | | |
| | | 2 | Voltage regulation rate $S_V$ | Semiconductor integrated circuits.Measuring method of voltage regulators GB/T 4377-2018 | Accredited only for: Voltage:-40V~40V Current:-1A~1A Maximum 48 channels | | |
| | | 3 | Current regulation Rate $S_T$ | Semiconductor integrated circuits.Measuring method of voltage regulators GB/T 4377-2018 | Accredited only for: Voltage:-40V~40V Current:-1A~1A Maximum 48 channels | | |
| 3 | IC（analogue switch） | 1 | Analog switch operating range $V_A$ | Semiconductor integrated circuits.Measuring method of analogue switch GB/T 14028-2018 | Accredited only for: Voltage:-40V~40V Current:-1A~1A Maximum 48 channels | | |
| 4 | IC（DC-DC Convertor） | 1 | Output voltage $V_o$ | The measuring methods of DC/DC converters for hybrid integrated circuits SJ 20646-1997 | Accredited only for: Voltage:-40V~40V Current:-1A~1A Maximum 48 channels | | |
| | | 2 | Output current $I_o$ | The measuring methods of DC/DC converters for hybrid integrated circuits SJ 20646-1997 | Accredited only for: Voltage:-40V~40V Current:-1A~1A Maximum 48 channels | | |

| | | 3 | Voltage regulation rate $S_V$ | The measuring methods of DC/DC converters for hybrid integrated circuits SJ 20646-1997 | Accredited only for: Voltage-40V~40V Current:-1A~1A Maximum 48 channels | | |
|---|---|---|---|---|---|---|---|
| | | 4 | Current regulation rate $S_I$ | The measuring methods of DC/DC converters for hybrid integrated circuits SJ 20646-1997 | Accredited only for: Voltage:-40V~40V Current:-1A~1A Maximum 48 channels | | |
| 5 | IC（microprocessors） | 1 | Input high level current $I_{IH}$ | Semiconductor devices Integrated circuits Part 2:Digital integrated circuits GB/T 17574-1998 | Accredited only for: Voltage:-1V~6V Current:-200mA~200mA Maximum 512 channels | | |
| | | 2 | Input low level current $I_{IL}$ | Semiconductor devices Integrated circuits Part 2:Digital integrated circuits GB/T 17574-1998 | Accredited only for: Voltage:-1V~6V Current:-200mA~200mA Maximum 512 channels | | |
| | | 3 | Static working current $I_{SB}$ | Semiconductor devices Integrated circuits Part 2:Digital integrated circuits GB/T 17574-1998 | Accredited only for: Voltage:-1V~6V Current: -200mA~200mA | | |
| | | 4 | Dynamic working current $I_A$ | Semiconductor devices Integrated circuits Part 2:Digital integrated circuits GB/T 17574-1998 | Accredited only for: Voltage:-1V~6V Current:-200mA~200mA Maximum 512 channels | | |
| | | 5 | Function test | Semiconductor devices Integrated circuits Part 2:Digital integrated circuits GB/T 17574-1998 | Accredited only for: Voltage:-1V~6V Current:-200mA~200mA Maximum 512 channels | | |
| | | 6 | Output high level voltage $V_{OH}$ | Semiconductor devices Integrated circuits Part 2:Digital integrated circuits GB/T 17574-1998 | Accredited only for: Voltage:-1V~6V Current:-200mA~200mA Maximum 512 channels | | |

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| | | 7 | Output low level voltage $V_{OL}$ | Semiconductor devices Integrated circuits<br>Part 2:Digital integrated circuits<br>GB/T 17574-1998 | Accredited only for:<br>Voltage:-1V~6V<br>Current:-200mA~200mA<br>Maximum 512 channels | | |
| | | 8 | Iutput high level voltage $V_{IH}$ | Semiconductor devices Integrated circuits<br>Part 2:Digital integrated circuits<br>GB/T 17574-1998 | Accredited only for:<br>Voltage:-1V~6V<br>Current:-200mA~200mA<br>Maximum 512 channels | | |
| | | 9 | Iutput low level voltage $V_{IL}$ | Semiconductor devices Integrated circuits<br>Part 2:Digital integrated circuits<br>GB/T 17574-1998 | Accredited only for:<br>Voltage:-1V~6V<br>Current:-200mA~200mA<br>Maximum 512 channels | | |
| 6 | Resistance (Fixed resistor、Metalster、Film resistor、Wire-wound resistor、Potentiometer) | 1 | Resistance value | Finxed resistors for use in electronic equipment<br>Part 1: Generic specification<br>GB/T 5729-2003 | Accredited only for:<br>Resistance range :<br>0.00001Ω~99.9999MΩ | 0.00001Ω~99.9999MΩ | |
| | | 2 | Terminal resistance | Potentiometers for electronic equipment<br>Part 1: General specification<br>GB/T 15298-1994 | Accredited only for:<br>Resistance range :<br>0.00001Ω~99.9999MΩ | 0.00001Ω~99.9999MΩ | |
| 7 | Diode (Zener diode、Switch-diode、Rectifier diode、Schottky Diode、TVS 、LED、Silicon power switching diode) | 1 | Forward voltage | Semiconductor devices discrete devices and integrated circuits<br>Part 2:Rectifier diodes<br>GB/T 4023-2015 | Only pulse method is used for testing;<br>Accredited only for:<br>Voltage: 0V~2000V,<br>Current: 0A~200A | Voltage: 0V~2000V,<br>Current: 0A~200A | |
| | | 2 | Reverse current | Semiconductor devices discrete devices and integrated circuits<br>Part 2:Rectifier diodes<br>GB/T 4023-2015 | Only direct-current method is used for testing;<br>Accredited only for:<br>Voltage: 0V~2000V,<br>Current: 0A~200A | Voltage: 0V~2000V,<br>Current: 0A~200A | |

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| | | 3 | Breakdown voltage | Semiconductor devices discrete devices and integrated circuits Part 2:Rectifier diodes GB/T 4023-2015 | Accredited only for: Voltage：0V~2000V, Current Range：0A~200A | Voltage：0V~2000V, Current：0A~200A | |
| | | 4 | Working voltage | Semiconductor devices-Discrete devices. part3:singal (including switching) and regulator diodes GB/T 6571-1995 | Accredited only for: Voltage：0V~2000V, Current Range：0A~200A | Voltage：0V~2000V, Current：0A~200A | |
| | | 5 | Differential resistance | Semiconductor devices-Discrete devices. part3:singal (including switching) and regulator diodes GB/T 6571-1995 | Accredited only for: Voltage：0V~2000V, Current Range：0A~200A | Voltage：0V~2000V, Current：0A~200A | |
| 8 | Triode（Switching triode、Power Transisitor） | 1 | Collector- Base electrode breakdown voltage | Semiconductor discrete devices and dntegrated circuits. Part 7: Bipolar transistors GB/T 4587-1994 | Accredited only for: Voltage：0V~2000V, Current：0A~200A | Voltage：0V~2000V, Current：0A~200A | |
| | | 2 | Emitter -Base electrode breakdown voltage | Semiconductor discrete devices and dntegrated circuits. Part 7: Bipolar transistors GB/T 4587-1994 | Accredited only for: Voltage：0V~2000V, Current：0A~200A | Voltage：0V~2000V, Current：0A~200A | |
| | | 3 | Collector-Base electrode cutoff current | Semiconductor discrete devices and dntegrated circuits. Part 7: Bipolar transistors GB/T 4587-1994 | Accredited only for: Voltage：0V~2000V, Current：0A~200A | Voltage：0V~2000V, Current：0A~200A | |
| | | 4 | Collector-Emitter Saturation voltage | Semiconductor discrete devices and dntegrated circuits. Part 7: Bipolar transistors GB/T 4587-1994 | Accredited only for: Voltage：0V~2000V, Current：0A~200A | Voltage：0V~2000V, Current：0A~200A | |
| | | 5 | Emitter-Base electrode cutoff current | Semiconductor discrete devices and dntegrated circuits. Part 7: Bipolar transistors GB/T 4587-1994 | Accredited only for: Voltage：0V~2000V, Current：0A~200A | Voltage：0V~2000V, Current：0A~200A | |

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| | | 6 | Collector-Emitter Cutoff current | Semiconductor discrete devices and dntegrated circuits. Part 7: Bipolar transistors GB/T 4587-1994 | Accredited only for: Voltage：0V~2000V, Current：0A~200A | Voltage：0V~2000V, Current：0A~200A | |
| | | 7 | Forward current transfer ratio of common-emitter | Semiconductor discrete devices and dntegrated circuits. Part 7: Bipolar transistors GB/T 4587-1994 | Accredited only for: Voltage：0V~2000V, Current：0A~200A | Voltage：0V~2000V, Current：0A~200A | |
| 9 | Field effect transistor（JFET、JGFET） | 1 | Drain-source breakdown voltage | Transistor Electrical Test Methods For Semiconductor Devices Part 3: Test Methods 3000 Through 3999 MIL-STD-750-3-2019 Method 3407.1 | Accredited only for: Voltage：0V~2000V, Current：0A~200A | Voltage：0V~2000V, Current：0A~200A | |
| | | 2 | Threshold voltage | Semiconductor devices.Discrete devices. Part 8:Field-effect transistors GB/T 4586-1994 Chapter IV Article 6 | Accredited only for: Voltage：0V~2000V, Current：0A~200A | Voltage：0V~2000V, Current：0A~200A | |
| | | 3 | Gate cutoff current | Semiconductor devices.Discrete devices. Part 8:Field-effect transistors GB/T 4586-1994 Chapter IV Article 2 | Accredited only for: Voltage：0V~2000V, Current：0A~200A | Voltage：0V~2000V, Current：0A~200A | |
| | | 4 | Drain current | Semiconductor devices.Discrete devices. Part 8:Field-effect transistors GB/T 4586-1994 Chapter IV Article 3 | Accredited only for: Voltage：0V~2000V, Current：0A~200A | Voltage：0V~2000V, Current：0A~200A | |

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| | | 5 | On-state-drain source resistance | Semiconductor devices.Discrete devices.<br>Part 8:Field-effect transistors<br>GB/T 4586-1994<br>Chapter IV Article 16 | Accredited only for:<br>Voltage: 0V~2000V,<br>Current: 0A~200A | Voltage: 0V~2000V,<br>Current: 0A~200A | |
| 10 | AECQ-100<br>Integrated circuits<br>Test | 1 | Preconditioning | Moisture/Reflow Sensitivity Classification fot Nonhermetic Surface Mount Devices<br>JEDEC J-STD-020F-2022 | Accredited only for surface mout devices | Temperature 25 ℃ to 150 ℃;<br>Humidity: 30% RH to 98% RH<br>Reflow welding temperature: 25℃ -300℃ | |
| | | | | Preconditioning of Nonhermetic Surface Mount Devices Prior to Reliability Testing<br>JEDEC JESD22-A113I-2020 | | | |
| | | 2 | Biased steady-state damp heat | Steady-state temperature-humidity bias life test<br>JEDEC JESD22-A101D.01-2021 | Test only: Range of conditions<br>Temperature : 25 ℃ to 150 ℃;<br>Humidity: 30% RH to 98% RH | Temperature:<br>25℃-150℃;<br>Humidity:<br>30%RH-98%RH | |
| | | 3 | Biased-HAST | Highly Accelerated Temperature and Humidity Stress Test(HAST)<br>JEDEC JESD22-A110E.01-2021 | Test only: Range of conditions<br>Temperature : 105℃ to 150 ℃;<br>Humidity: 65% RH to 100% RH | Temperature:<br>105℃～150℃;<br>Humidity:<br>65%RH-100%RH | |
| | | 4 | Autoclave | Acccelerated Moisture Resistance-Unbiased Autoclave<br>JEDEC JESD22-A102E-2015 | Test only: Range of conditions<br>Temperature : 100℃ to 134 ℃;<br>Humidity: 100% RH | Temperature:<br>100℃-134℃;<br>Humidity:100%RH | |

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| | | 5 | Unbiased-HAST | Acccelerated Moisture Resistance-Unbiased HAST JEDEC JESD22-A118B.01-2021 | Test only: Range of conditions Temperature ：105℃ to 150 ℃； Humidity: 65% RH to 100% RH | Temperature: 105℃-150℃； Humidity: 65%RH～100%RH | |
| | | 6 | Temperature-Humidity （without Bias） | Steady-State Temperature-Humidity Bias Life Test JEDEC JESD22-A101D.01-2021 | Test only: Range of conditions Temperature ：25℃ to 150 ℃； Humidity: 30% RH to 98% RH | Temperature: 25℃-150℃； Humidity: 30%RH-98%RH | |
| | | 7 | Temperature Cycling | Temperature Cycling JEDEC JESD22-A104F.01-2023 | Test only: Range of conditions Temperature range: -65℃ -150℃ | Temperature: -65℃-150℃； | |
| | | 8 | High Temperature Storage Life | High Temperature Storage Life JEDEC JESD22-A103E.01-2021 | Accredited only for condition A、B、C、D | Temperature: 25℃-150℃； | |
| | | 9 | High Temperature operating Life | Temperatue,Bias,and Operating Life JEDEC JESD22- A108G-2022 | Accredited only for Temperature: 25℃～150℃ | Temperature: 25℃-150℃； | |
| | | 10 | Early Life Failure Rate | Early Life Failure Rate AEC-Q100-008A-2003 | Accredited only for Temperature: 25℃～150℃ | Temperature: 25℃-150℃； | |
| | | 11 | NVM Endurance,Data Retention,and Operational Life | Non-Volatile Memory Program/Erase Endurance, Data Retention,and Operational life test AEC-Q100-005D1-2012 | Accredited only for Temperature: 25℃～150℃ | Temperature: 25℃-150℃； | |

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| | | 12 | Wire Bond Shear | Wire Bond Shear Test<br>AEC-Q100-001C-1998 | ALL | Shear force ≤100 kg | |
| | | 13 | Wire Pond Pull | Test Method Standard Microcircuits<br>MIL-STD-883L-2019<br>Method 2011.10 | Accredited only for condition C、D;<br>tension ≤100g | Tensile≤100g | |
| | | 14 | Solderability | Solderability Tests for Component Leads,Terminations, Lugs,Terminals and Wires<br>J-STD-002E-2017 | Dip and reflow soldering only | Temperature:<br>25℃-350℃ | |
| | | 15 | Physical Dimensions | Physical Dimensions<br>JEDEC JESD22-B100B-2003 | Size ≤400 mm | Accuracy: 0.0001 mm | |
| | | 16 | Solder Ball Shear | Solder Ball Shear Test<br>AEC-Q100-010A-2003 | ALL | Shear force ≤100 kg | |
| | | 17 | Lead Integrity | Lead Integrity<br>JEDEC JESD22-B105E-2017 | Accredited only for condition A、B | Pull ≤4 kg | |
| | | 18 | Mechanical Shock | Mechanical Shock-Device and Subassembly<br>JEDEC JESD22-B110B.01-2019 | Accredited only for condition A、B、F | Acceleration≤50000g | |
| | | 19 | Variable Frequency Vibration | Vibration,Variable Frequency<br>JEDEC JESD22-B103B.01-2016 | Accredited only for Sweep frequency vibration condition 1 | Frequency range:<br>5HZ~2000HZ<br>Acceleration≤50g | |
| | | 20 | Constant Acceleration test | Test Method Standard Microcircuits<br>MIL-STD-883L-2019<br>Method 2001.4 | Accredited only for condition A-E | Acceleration≤50000g | |

| | | 21 | Sealing test | Test Method Standard Microcircuits MIL-STD-883L-2019 Method 1014.17 | Accredited only for condition A、C | Fine Leak:Tracer gas He Gross Leak:Fluorocarbon | |
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| | | 22 | Die Shear | Test Method Standard Microcircuits MIL-STD-883L-2019 Method 2019.10 | Accredited only for surface mout devices | Shear force ≤100 kg | |
| 11 | AECQ-101 Discrete devices Test | 1 | Preconditioning | Preconditioning of Nonhermetic Surface Mount Devices Prior to Reliability Testing JEDEC JESD22-A113I-2020 | Accredited only for surface mout devices | Temperature 25 ℃ to 150 ℃; Humidity: 30% RH to 98% RH Reflow welding temperature: 25℃ -300℃ | |
| | | | | Moisture/Reflow Sensitivity Classification fot Nonhermetic Surface Mount Devices JEDEC J-STD-020F-2022 | | | |
| | | 2 | Visual | External Visual JEDEC JESD22- B101D-2022 | Magnification: 7.5X~100X | Magnification: 7.5X~100X | |
| | | 3 | High Temperature Revere Bias test | Test Method Standard Environmental Test Methods For Semiconductor Devices. Part 1:Test Methods 1000 Through 1999 MIL-STD-750-1A -2016 Method 1038.5、1039.4 | Accredited only for condition A | Voltage≤1500V Temperature: 25℃-175℃; | |
| | | 4 | High Temperature Gate Bias test | Temperatue,Bias,and Operating Life JEDEC JESD22 A108G-2022 | Test only: Range of conditions Voltage≤1500V Temperature: 25~175℃ | Voltage≤1500V Temperature: 25℃-175℃; | |
| | | 5 | Temperature Cycling | Temperature Cycling JEDEC JESD22-A104F.01-2023 | Test only: Range of conditions Temperature: -65℃-150℃ | Temperature: -65℃ -150℃ | |

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| | | 6 | Unbiased Highly Accelerated Stress Test | Acccelerated Moisture Resistance-Unbiased HAST JEDEC JESD22-A118B.01-2021 | Test only: Range of conditions Temperature:105℃-150℃; Humidity:65%RH～100%RH | Temperature: 105℃-150℃; Humidity: 65%RH～100%RH | |
| | | 7 | Highly Accelerated Stress Test | Highly Accelerated Temperature and Humidity Stress Test(HAST) JEDEC JESD22-A110E.01-2021 | Test only: Range of conditions Temperature:105℃-150℃; Humidity:65%RH～100%RH | Temperature: 105℃-150℃; Humidity: 65%RH～100%RH | |
| | | 8 | High Humidity High Tem. Reverse Bias | Steady-State Temperature-Humidity Bias Life Test JEDEC JESD22-A101D.01-2021 | Test only: Range of conditions Temperature:25℃-150℃; Humidity:30%RH～98%RH | Temperature: 25℃-150℃; Humidity: 30%RH～98%RH | |
| | | 9 | Intermittent Operational Life | Test Method Standard Environmental Test Methods For Semiconductor Devices. Part 1:Test Methods 1000 Through 1999 MIL-STD-750-1A-2016 Method 1037.3 | For no heat dissipation conditions only | Power≤10W | |
| | | 10 | Physical Dimension | Physical Dimensions JEDEC JESD22-B100B-2003 | Size ≤400 mm | Accuracy: 0.0001 mm | |
| | | 11 | Terminal Strength | Test Method Standard Mechanical Test Methods For Semiconductor Devices Part 2: Test Methods 2001 Through 2999 MIL-STD-750-2A-2018 Method 2036.5 | Accredited only for condition A、E | Pulling ≤4 kg | |

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| | | 12 | Resistance to Solvents | Mark Permanency<br>JEDEC JESD22-B107D-2011 | Only for ink marking | Mixed solvent 1: pure isopropyl alcohol 75 jet fuel<br>Mixed solvent 2: turpentine<br>Mixed solvent 3: Deionized water, ethylene glycol - butyl ether, monoethanolamine | |
| | | 13 | Constant Acceleration | Test Method Standard Mechanical Test Methods For Semiconductor Devices Part 2: Test Methods 2001 Through 2999 MIL-STD-750-2A-2018<br>Method 2006.2 | Accredited only for condition A-E | Acceleration≤5000g | |
| | | 14 | Variable Frequency Vibration | Vibration,Variable Frequency<br>JEDEC JESD22-B103B.01-2016 | Accredited only for Sweep vibration condition 1 | Frequency range: 5HZ~2000HZ<br>Acceleration ≤50g | |
| | | 15 | Mechanical Shock | Mechanical Shock-Device and Subassembly<br>JEDEC JESD22-B110B.01-2019 | Accredited only for condition A、B、F | Acceleration≤5000g | |
| | | 16 | Sealing test | Hermiticity<br>JEDEC JESD22-A109B-2011 | Accredited only for condition A、C | Fine Leak:Tracer gas He<br>Gross Leak:Fluorocarbon | |
| | | 17 | Resistance to Solder Heat | Evaluation Procedure for Determing Capability Bottom Side Board Attach by Full Body Solder Immersion of Small Surface Mount SOLID state Devices<br>JEDEC JESD22-A111B-2018 | Dip and reflow soldering only | Temperature: ≤350℃ | |

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| | | | | Resistance to Solder Shock for Through-Hole Mounted Devices JEDEC JESD22-B106E-2016 | Dip and reflow soldering only | Temperature: ≤350℃ | |
| | | 18 | Solderrability | Solderability Tests for Component Leads, Terminations, Lugs, Terminals and Wires J-STD-002E-2017 | Dip and reflow soldering only | Temperature: 25℃-350℃ | |
| | | 19 | Wire Bond pull | Test Method Standard Mechanical Test Methods For Semiconductor Devices Part 2: Test Methods 2001 Through 2999 MIL-STD-750-2A-2018 | ALL | Pulling ≤100kg | |
| | | 20 | Wire Bond Shear | Wire Bond Shear Test AEC-Q101-003A-2005 | ALL | Shear force≤100kg | |
| | | 21 | Die Shear | Test Method Standard Mechanical Test Methods For Semiconductor Devices Part 2: Test Methods 2001 Through 2999 MIL-STD-750-2A-2018 Method 2017.3 | ALL | Shear force≤100kg | |